ABSTRACT OF THE DISCLOSURE

A method of photolithographically forming an integrated circuit feature, such as a conductive structure, for example a gate electrode (15), or such as a patterned insulator feature, is disclosed. A critical dimension (CD) for a photolithography process defines a minimum line width of photoresist or other masking material that may be patterned by the process. A photomask (20, 30, 40, 50, 60) has a mask feature (25, 35, 45, 55, 65) that has varying width portions along its length. The wider portions have a width (L_1) that is at or above the critical dimension of the process, while the narrower portions have a width (L_2) that is below the critical dimension of the process. In the case of a patterned etch of a conductor, photoexposure and etching of conductive material using the photomask (20, 30, 40, 50, 60) defines a gate electrode (15) for a transistor (10) that has a higher drive current than a transistor having a uniform gate width at the critical dimension.